

NCE30TD60BT

600V, 30A, Trench FS II Fast IGBT

General Description:

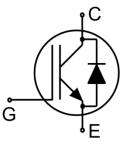
Using NCE's proprietary trench design and advanced FS (Field Stop) second generation technology, the 600V Trench FS II IGBT offers superior conduction and switching performances, and easy parallel operation;

Features

- Trench FSII Technology offering
- Very low V_{CE(sat)}
- High speed switching
- Positive temperature coefficient in V_{CE(sat)}
- Very tight parameter distribution
- High ruggedness, temperature stable behavior

Application

- Air Condition
- Inverters
- Motor drives



Schematic diagram

Package Marking and Ordering Information

Device	Device Package	Device Marking		
NCE30TD60BT	TO-247	NCE30TD60BT		



Absolute Maximum Ratings (T_C=25°C unless otherwise noted)

TO-247

Symbol	Parameter	Value	Units
Vces	Collector-Emitter Voltage	600	V
V_{GES}	Gate- Emitter Voltage	±30	V
	Collector Current	60	Α
Ic	Collector Current @T _C = 100°C	30	Α
I _{Cplus}	Pulsed Collector Current, tp limited by Tjmax	90	Α
-	turn off safe operating area, V _{CE} =600V, Tj=150°C	90	Α
I _F	Diode Continuous Forward Current @T _C = 100°C	30	Α
I _{FM}	Diode Maximum Forward Current	90	Α
В	Power Dissipation @ T _C = 25°C	190	W
P _D	Power Dissipation @T _C = 100 °C	95	W
T_J, T_{stg}	Operating Junction and Storage Temperature Range	-55 to +175	°C
TL	Maximum Temperature for Soldering	260	°C
t _{sc}	Short circuit withstand time V _{GE} =15V, V _{CC} ≤400V, Allowed number of short circuits<1000Time between short circuits:≥1.0s,T _j ≤150°C	5	us

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Thermal Characteristic

Symbol	Parameter	Value	Units
Rejc	Thermal Resistance, Junction to case for IGBT	0.78	°C/W
R _θ JC	Thermal Resistance, Junction to case for Diode	1.08	°C/W
RθJA	Thermal Resistance, Junction to Ambient	40	°C/W

Electrical Characteristics (Tc=25°C unless otherwise noted)

0		Test Conditions		Value			
Symbol	Parameter			Min.	Тур.	Max.	Units
Static Chara	cteristics				•	· ·	
V _{(BR)CES}	Collector-Emitter Breakdown Voltage	V _{GE} =0V	,I _{CE} =1mA	600			V
Ices	Collector-Emitter Leakage Current	V _{GE} =0V	V _{CE} =600V			4	uA
I _{GES(F)}	Gate to Emitter Forward Leakage	V _{GE} =+30	V,V _{CE} =0V			200	nA
I _{GES(R)}	Gate to Source Reverse Leakage	V _{GE} =-30	V,Vce =0V			200	nA
V	O-ll-stan Freittan O-tombian Valtana	Ic=30A	Tj=25°C		1.7	1.9	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$V_{\text{GE}}=15V$	Tj=150°C		1.9		V
$V_{GE(th)}$	Gate Threshold Voltage	Ic=1mA,Vc==VgE		4.0	5.0	6.0	V
Dynamic Cha	aracteristics						
Cies	Input Capacitance	V _{CE} =25V,V _{GE} =0V, f=1MHz			3552		pF
Coes	Output Capacitance				106		
Cres	Reverse Transfer Capacitance				67		
Qg	Total Gate Charge	Vcc=480V, Ic=30A VgE=15V			132		nC
Qge	Gate to Emitter Charge				28		
Qgc	Gate to Collector Charge				54		
I _{C(SC)}	Short circuit collector current Max.1000 short circuits Time between short circuits: ≥1.0s	V _{GE} =15V,V _{CC} ≤400V, t _{SC} ≤5us,Tj≤150°C			190		А
Switching Cl	naracteristics						
$t_{d(ON)}$	Turn-on Delay Time				19		
t _r	Rise Time				17		20
$t_{\text{d}(\text{OFF})}$	Turn-Off Delay Time	Vcc=400V,Ic=30A			166		ns
t f	Fall Time	$V_{GE}=0/15V$, $R_g=5\Omega$			16		
Eon	Turn-On Switching Loss	Inductive Load			0.36		
E _{off}	Turn-Off Switching Loss				0.32		mJ
Ets	Total Switching Loss				0.68		

Electrical Characteristics of the Diode (Tc= 25°C unless otherwise specified):

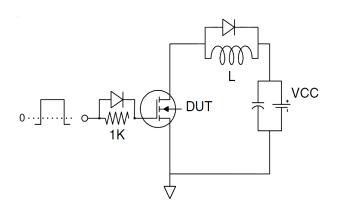
Cumbal	Parameter	Test Conditions	Rating			l lnita
Symbol			Min.	Тур.	Max.	Units
V_{FM}	Diode Forward Voltage	I _F =30A		1.7	1.9	V
Trr	Reverse Recovery Time			178		ns
I _{RRM}	Diode Peak Reverse Recovery Current	I _F =30A, di/dt=200A/us		4		Α
Qrr	Reverse Recovery Charge			0.4		uC
Pulse width $t_p \le 380 \mu s, \delta \le 2\%$						



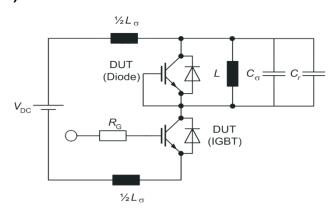
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Test Circuit

1) Gate Charge Test Circuit

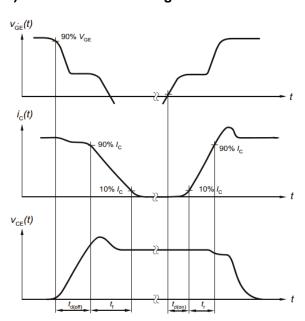


2) Switch Time Test Circuit

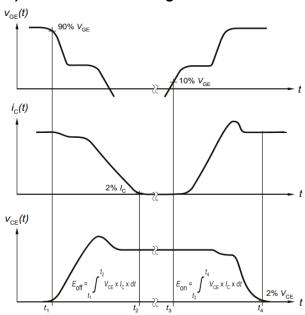


Switching characteristics

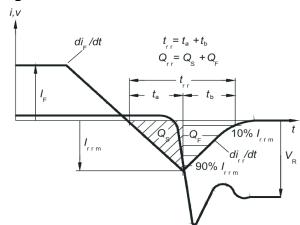
1) Definition of switching times



2) Definition of switching losses



3) Definition of diode switching characteristics





Typical Electrical and Thermal Characteristics

Figure 1 Output Characteristics

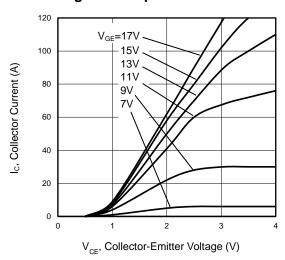


Figure 3 V_{CEsat} vs. Case Temperature

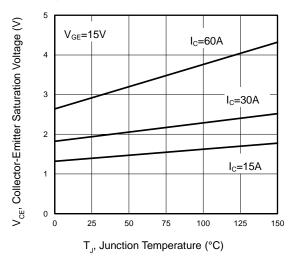


Figure 5 Capacitance Characteristics

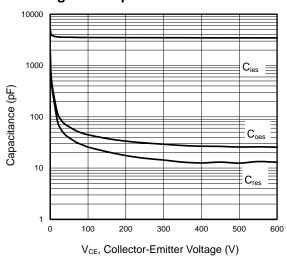


Figure 2 Transfer Characteristics

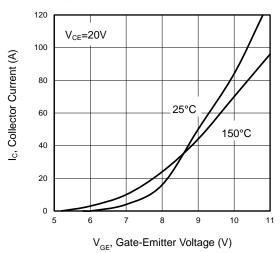


Figure 4 Saturation Voltage vs. V_{GE}

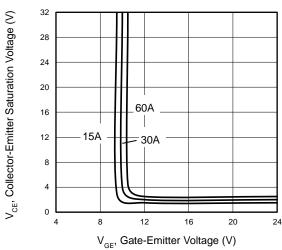
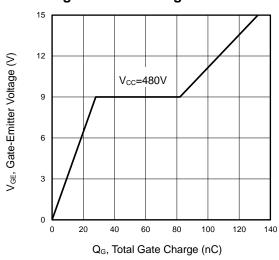


Figure 6 Gate charge waveform





Typical Electrical and Thermal Characteristics

Figure 7 Gate-emitter Threshold Voltage as a Function of Junction Temperature

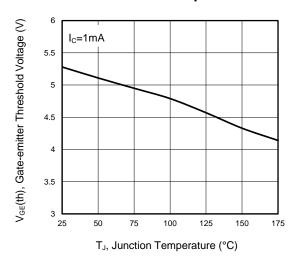


Figure 9 Typical Switching Times as a Function of Gate Resistor

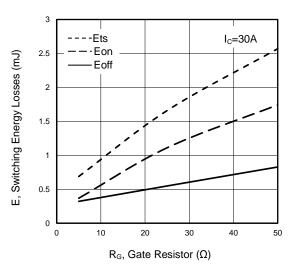


Figure 11 Typical Collector-emitter Saturation
Voltage as a function of Collector Current

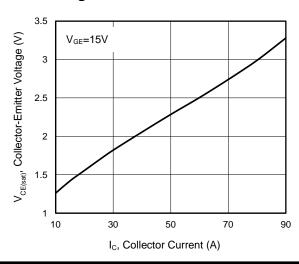
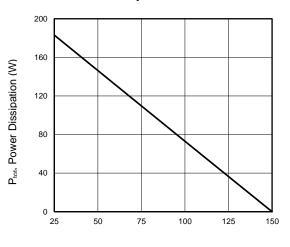
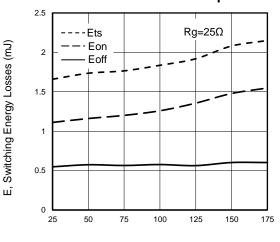


Figure 8 Power Dissipation as a Function of Case Temperature



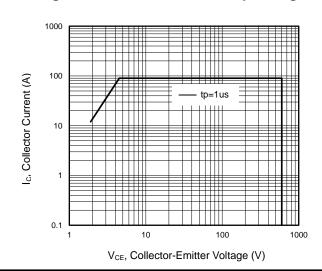
T_C, Case Temperature (°C)

Figure 10 Typical Switching Times as a Function of Junction Temperature



T_J, Junction Temperature (°C)

Figure 13 Forward Bias Safe Operating Area

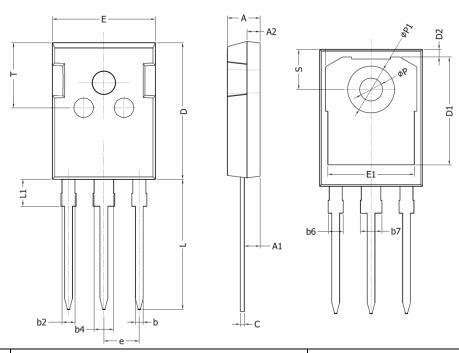


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TO-247-3L Package Information



Symbol	Dimensions I	n Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	4.90	5.10	0.193	0.201	
A1	2.31	2.51	0.091	0.099	
A2	1.9	2.1	0.075	0.083	
b	1.16	1.26	0.046	0.050	
b2	1.96	2.06	0.077	0.081	
b4	2.96	3.06	0.117	0.120	
b6	-	2.25	-	0.089	
b7	-	3.25	-	0.128	
С	0.59	0.66	0.023	0.026	
D	20.90	21.10	0.823	0.831	
D1	16.25	16.85	0.640	0.663	
D2	1.05	1.35	0.041	0.053	
Е	15.70	15.90	0.618	0.626	
E1	13.10	13.50	0.516	0.531	
е	5.436 BSC		0.214 BS	С	
L	19.80	20.10	0.780	0.791	
L1	-	4.30	-	0.169	
Р	3.40	3.60	0.134	0.142	
P1	7.00	7.40	0.276	0.291	
S	6.05	6.25	0.238	0.246	
Т	9.80	10.20	0.386	0.402	



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